# **74AHC1GU04**

#### Inverter

Rev. 05 — 10 July 2007

**Product data sheet** 

### 1. General description

The 74AHC1GU04 is a high-speed Si-gate CMOS device. It provides an inverting single stage function.

#### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - HBM JESD22-A114E: exceeds 2000 V
     MM JESD22-A115-A: exceeds 200 V
     CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

## 3. Ordering information

Table 1. Ordering information

Type number	Package	Package											
	Temperature range	Name	Description	Version									
74AHC1GU04GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1									
74AHC1GU04GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753									

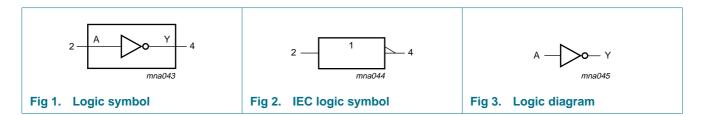
### 4. Marking

Table 2. Marking codes

Type number	Marking
74AHC1GU04GW	AD
74AHC1GU04GV	AU4

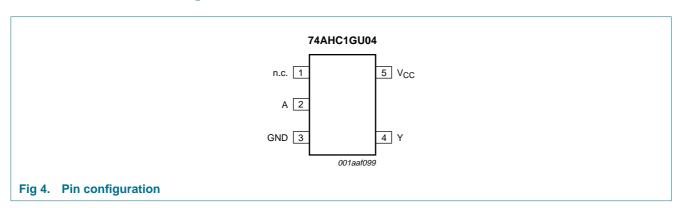


# 5. Functional diagram



# 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
Α	2	data input
GND	3	ground (0 V)
Υ	4	data output
$V_{CC}$	5	supply voltage

# 7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output
A	Υ
L	Н
H	L

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_1 < -0.5 \text{ V}$	-20	-	mA
$V_{I}$	input voltage		[ <u>1</u> ] -0.5	+7.0	V
$I_{OK}$	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
$I_{CC}$	supply current		-	75	mA
$I_{GND}$	ground current		<b>-75</b>	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	ns/V
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	ns/V

### 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C 1	to +85 °C	–40 °C t	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0 \text{ V}$	1.7	-	-	1.7	-	1.7	-	V
		V <sub>CC</sub> = 3.0 V	2.4	-	-	2.4	-	2.4	-	V
		$V_{CC} = 5.5 \text{ V}$	4.4	-	-	4.4	-	4.4	-	V
$V_{IL}$	LOW-level	$V_{CC} = 2.0V$	-	-	0.3	-	0.3	-	0.3	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	-	-	0.6	-	0.6	-	0.6	V
		$V_{CC} = 5.5 \text{ V}$	-	-	1.1	-	1.1	-	1.1	V

<sup>[2]</sup> For both TSSOP5 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

**Table 7. Static characteristics** ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
$V_{OH}$	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$	'				'			
	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O} = -50 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

# 11. Dynamic characteristics

Table 8. Dynamic characteristics

 $GND = 0 \ V$ ;  $t_f = t_f = \le 3.0 \ \text{ns.}$  For test circuit see Figure 6.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	1
t <sub>pd</sub>	propagation	A to Y; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C <sub>L</sub> = 15 pF		-	3.4	7.1	1.0	8.5	1.0	10.0	ns
		$C_L = 50 pF$		-	4.9	10.6	1.0	12.0	1.0	13.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	2.6	5.5	1.0	6.0	1.0	7.0	ns
		$C_L = 50 pF$		-	3.6	7.0	1.0	8.0	1.0	9.0	ns
C <sub>PD</sub> power dissipation capacitance		sipation $V_I = GND$ to $V_{CC}$		-	14	-	-	-	-	-	pF

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

<sup>[2]</sup> Typical values are measured at  $V_{CC} = 3.3 \text{ V}$ .

<sup>[3]</sup> Typical values are measured at  $V_{CC}$  = 5.0 V.

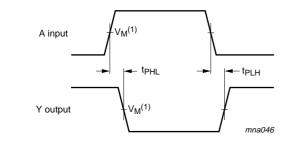
<sup>[4]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu$ W).  $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$   $f_i$  = input frequency in MHz;

 $f_o$  = output frequency in MHz;

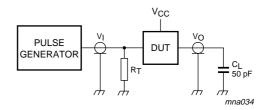
C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in Volts.

### 12. Waveforms



 $V_M = 0.5 \times V_{CC}$ ;  $V_I = GND$  to  $V_{CC}$ .



Test data is given in Table 8.

Definitions for test circuit:

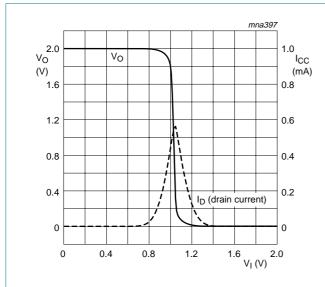
 $C_L$  = Load capacitance including jig and probe capacitance.

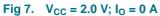
 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

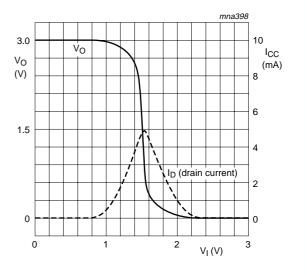
Fig 5. The input (A) to output (Y) propagation delay times

Fig 6. Load circuitry for switching times

# 13. Typical transfer characteristics

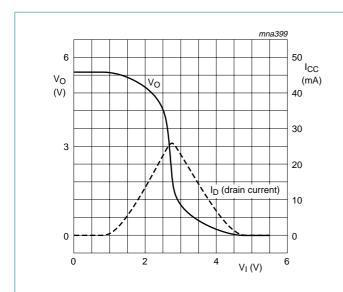


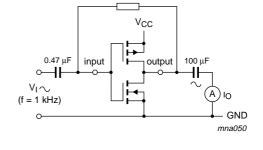




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Fig 8.  $V_{CC} = 3.0 \text{ V}$ ;  $I_{O} = 0 \text{ A}$ 





 $R_{bias} = 560 \text{ k}\Omega$ 

Fig 9.  $V_{CC} = 5.5 \text{ V}$ ;  $I_O = 0 \text{ A}$ 

Fig 10. Test set-up for measuring forward transconductance  $g_{fs} = \Delta I_O/\Delta V_I$  at  $V_O$  is constant

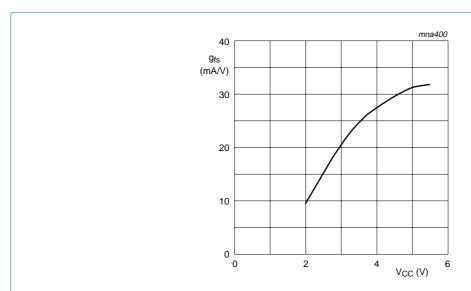


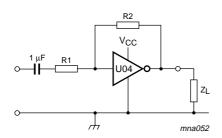
Fig 11. Typical forward transconductance  $g_{fs}$  as a function of the supply voltage at  $T_{amb}$  = 25 °C

# 14. Application information

Some applications are:

- Linear amplifier (see Figure 12)
- In crystal oscillator design (see Figure 13)

Remark: All values given are typical unless otherwise specified.



Maximum  $V_{o(p\text{-}p)}$  =  $V_{CC}-1.5$  V centered at  $0.5\times V_{CC}.$ 

$$G_v = -\frac{G_{ol}}{I + \frac{RI}{R2}(I + G_{ol})}$$

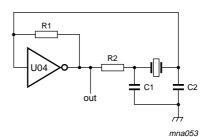
 $G_{ol}$  = open loop gain

G<sub>v</sub> = voltage gain

 $R1 \ge 3 \text{ k}\Omega, R2 \le 1 \text{ M}\Omega$ 

 $Z_L > 10 \text{ k}\Omega; G_{ol} = 20 \text{ (typ.)}$ 

Typical unity gain bandwidth product is 5 MHz.



C1 = 47 pF (typ.)

C2 = 22 pF (typ.)

R1 = 1 M $\Omega$  to 10 M $\Omega$  (typ.)

R2 optimum value depends on the frequency and required stability against changes in  $V_{CC}$  or average minimum  $I_{CC}$  ( $I_{CC}$  is typically 2 mA at  $V_{CC}$  = 3 V and f = 1 MHz).

Fig 12. Used as a linear amplifier

Fig 13. Crystal oscillator configuration

Table 9. External components for resonator (f < 1 MHz)

All values given are typical and must be used as an initial set-up.

Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	22 M $\Omega$	220 k $\Omega$	56 pF	20 pF
16 kHz to 24.9 kHz	22 M $\Omega$	220 k $\Omega$	56 pF	10 pF
25 kHz to 54.9 kHz	22 M $\Omega$	100 k $Ω$	56 pF	10 pF
55 kHz to 129.9 kHz	22 M $\Omega$	100 k $Ω$	47 pF	5 pF
130 kHz to 199.9 kHz	22 MΩ	47 kΩ	47 pF	5 pF
200 kHz to 349.9 kHz	22 MΩ	47 kΩ	47 pF	5 pF
350 kHz to 600 kHz	22 M $\Omega$	47 kΩ	47 pF	5 pF

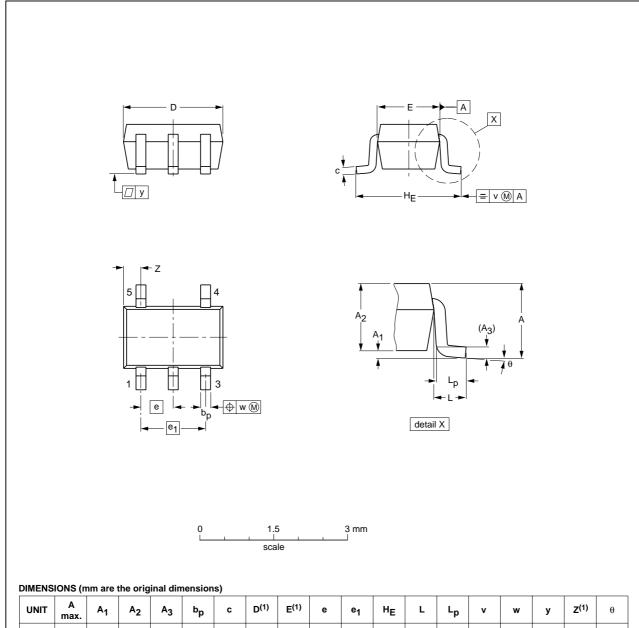
Table 10. Optimum value for R2

Frequency	R2	Optimum for
3 kHz	$2.0~\text{k}\Omega$	minimum required I <sub>CC</sub>
	$8.0~\text{k}\Omega$	minimum influence due to change in V <sub>CC</sub>
6 kHz	1.0 kΩ	minimum required I <sub>CC</sub>
	$4.7~\text{k}\Omega$	minimum influence by V <sub>CC</sub>
10 kHz	$0.5~\mathrm{k}\Omega$	minimum required I <sub>CC</sub>
	$2.0~\text{k}\Omega$	minimum influence by V <sub>CC</sub>
14 kHz	$0.5~\mathrm{k}\Omega$	minimum required I <sub>CC</sub>
	$1.0~\mathrm{k}\Omega$	minimum influence by V <sub>CC</sub>
>14 kHz	-	replace R2 by C3 with a typical value of 35 pF

# 15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	HE	L	Lp	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT353-1		MO-203	SC-88A			<del>-00-09-01</del> 03-02-19

Fig 14. Package outline SOT353-1 (TSSOP5)

#### Plastic surface-mounted package; 5 leads

SOT753

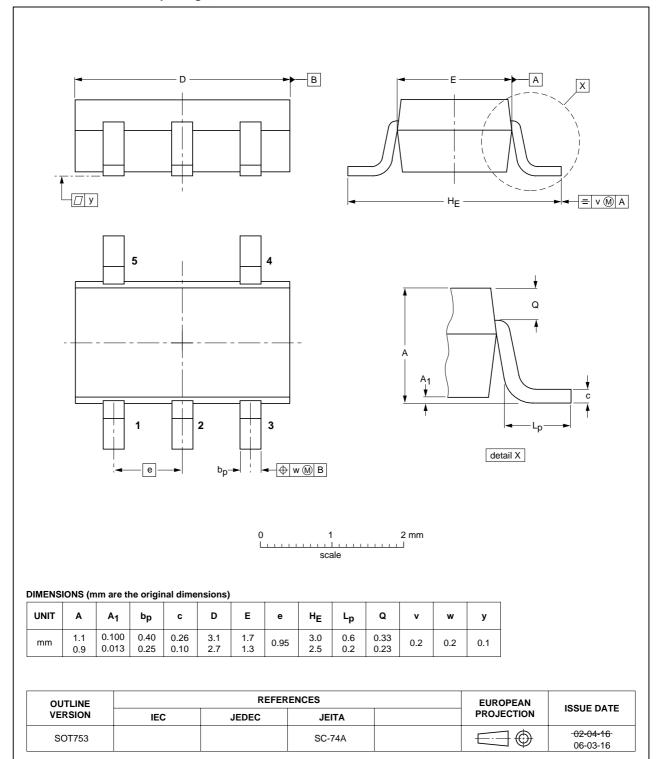


Fig 15. Package outline SOT753 (SC-74A)

### 16. Abbreviations

### Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 17. Revision history

#### Table 12. Revision history

	_			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC1GU04_5	20070710	Product data sheet	-	74AHC1GU04_4
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	with the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the n	ew company name whe	ere appropriate.
	<ul> <li>Package S</li> </ul>	OT353 changed to SOT353-	-1 in Section 3 and Section 3	tion 15.
	<ul> <li>Quick refer</li> </ul>	ence data and Soldering see	ctions removed.	
74AHC1GU04_4	20020528	Product specification	-	74AHC1GU04_3
74AHC1GU04_3	20020215	Product specification	-	74AHC1GU04_2
74AHC1GU04_2	20010427	Product specification	-	74AHC1GU04_1
74AHC1GU04_1	19990519	Product specification	-	-

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#### 18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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